NEW PRODUCT

Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D T_A = +25°C
Q2	40V	24mΩ @ V_{GS} = 10V	9.0A
		32mΩ @ V_{GS} = 4.5V	7.8A
Q1	-40V	45mΩ @ V_{GS} = -10V	-6.5A
		55mΩ @ V_{GS} = -4.5V	-5.9A

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description

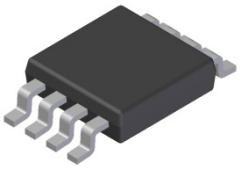
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Mechanical Data

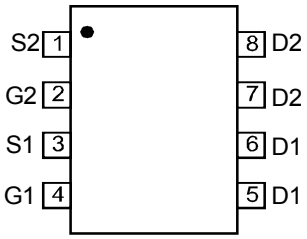
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (approximate)

Applications

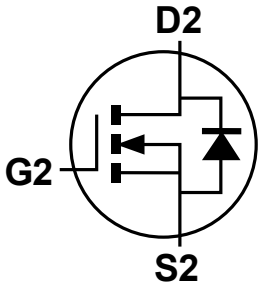
- DC-DC Converters
- Power Management Functions
- Backlighting



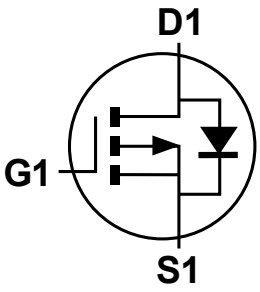
Top View



TOP VIEW
Internal Schematic



N-Channel MOSFET



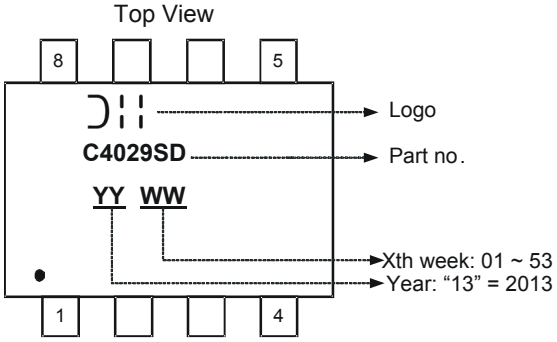
P-Channel MOSFET

Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMC4029SSD-13	Standard	SO-8	2,500/Tape & Reel
DMC4029SSDQ-13	Automotive	SO-8	2,500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value_Q2	Value_Q1	Units
Drain-Source Voltage			V_{DSS}	40	-40	V
Gate-Source Voltage			V_{GSS}	±20	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	7.0 5.6	-5.1 -4.1	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	9.0 7.2	-6.5 -5.2	A
Maximum Body Diode Forward Current (Note 7)			I_S	2.5	-2.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	70	-40	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	98	°C/W
	t<10s		59	
Total Power Dissipation (Note 7)	T_A = +25°C	P_D	1.8	W
	T_A = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	$R_{\theta JA}$	71	°C/W
	t<10s		43	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	11.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics N-Channel Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	15	24	mΩ	V_{GS} = 10V, I_D = 6A
		—	20	32		V_{GS} = 4.5V, I_D = 5A
Diode Forward Voltage	V_{SD}	—	0.7	1.0	V	V_{GS} = 0V, I_S = 1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1060	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	84	—		
Reverse Transfer Capacitance	C_{rss}	—	58	—		
Gate Resistance	R_G	—	1.6	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	8.8	—	nC	V_{DS} = 20V, I_D = 8A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	19.1	—		
Gate-Source Charge	Q_{gs}	—	3.0	—		
Gate-Drain Charge	Q_{gd}	—	2.5	—		
Turn-On Delay Time	$t_{D(on)}$	—	5.3	—	nS	V_{DD} = 25V, R_L = 2.5Ω V_{GS} = 10V, R_G = 3Ω
Turn-On Rise Time	t_r	—	7.1	—		
Turn-Off Delay Time	$t_{D(off)}$	—	15.1	—		
Turn-Off Fall Time	t_f	—	4.8	—		
Body Diode Reverse Recovery Time	t_{rr}	—	10.5	—	nS	I_F = 8A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{rr}	—	4.15	—	nC	I_F = 8A, di/dt = 100A/µs

NEW PRODUCT

Electrical Characteristics P-Channel Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-40	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	V_{DS} = -40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	-3.0	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	33	45	mΩ	V_{GS} = -10V, I_D = -5A
		—	40	55		V_{GS} = -4.5V, I_D = -4A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.0	V	V_{GS} = 0V, I_S = -1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1154	—	pF	V_{DS} = -20V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	84	—		
Reverse Transfer Capacitance	C_{rss}	—	66	—		
Gate Resistance	R_G	—	12.6	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	10.6	—	nC	V_{DS} = -20V, I_D = -4.9A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	21.5	—		
Gate-Source Charge	Q_{gs}	—	2.2	—		
Gate-Drain Charge	Q_{gd}	—	3.3	—		
Turn-On Delay Time	$t_{D(on)}$	—	8.7	—	nS	V_{DS} = -20V, I_D = -3.9A V_{GS} = -4.5V, R_G = 1Ω
Turn-On Rise Time	t_r	—	19.6	—		
Turn-Off Delay Time	$t_{D(off)}$	—	34.9	—		
Turn-Off Fall Time	t_f	—	25.5	—		
Body Diode Reverse Recovery Time	t_{rr}	—	9.61	—	nS	I_S = -3.9A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	—	3.3	—	nC	I_S = -3.9A, dI/dt = 100A/μs

Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

N-Channel Q2

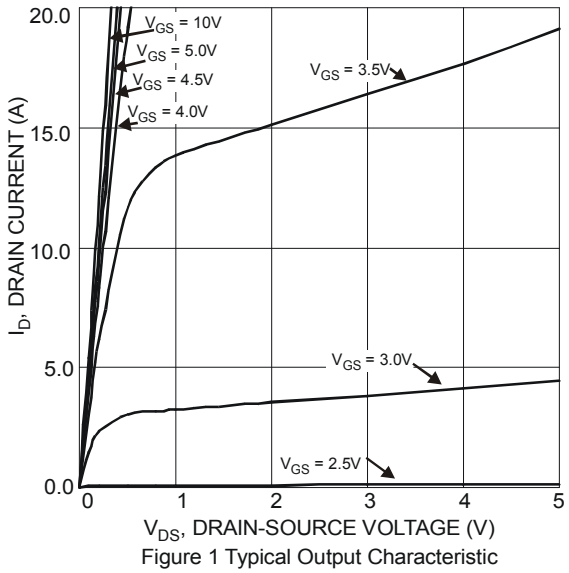


Figure 1 Typical Output Characteristic

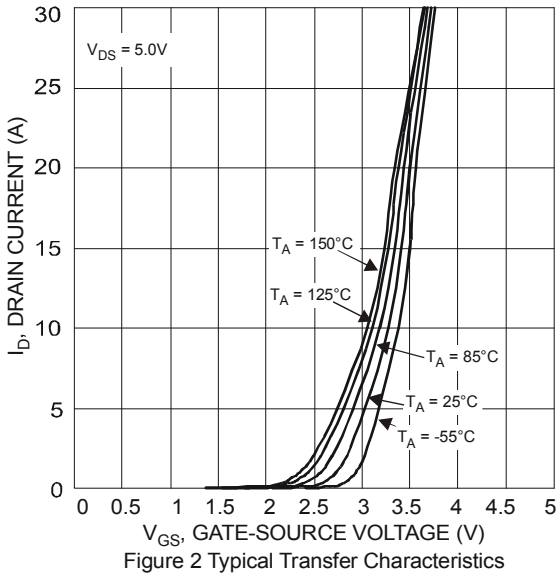


Figure 2 Typical Transfer Characteristics

NEW PRODUCT

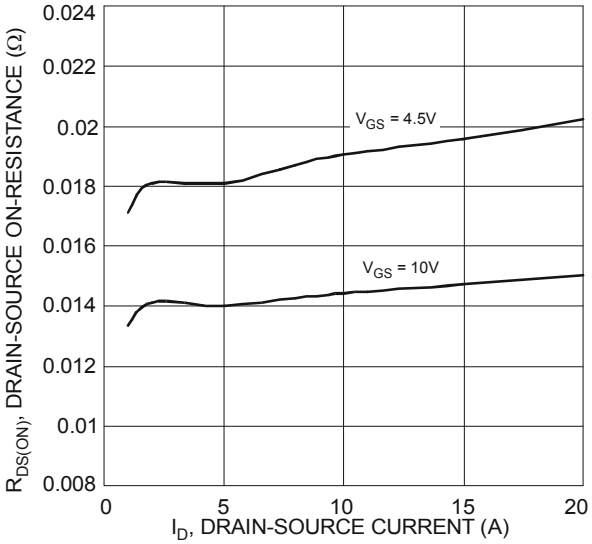


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

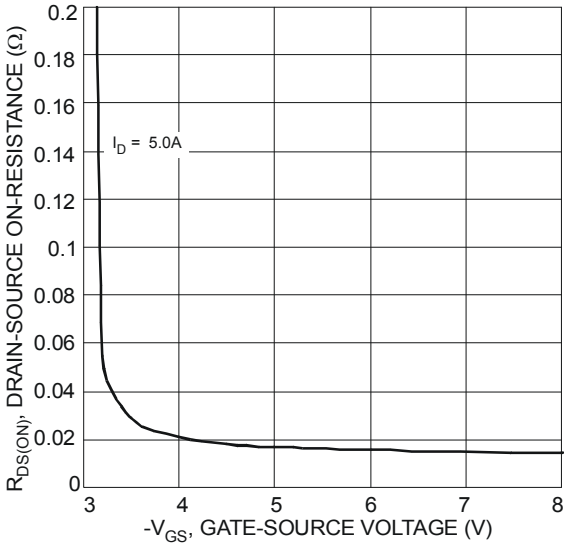


Figure 4 Typical Transfer Characteristic

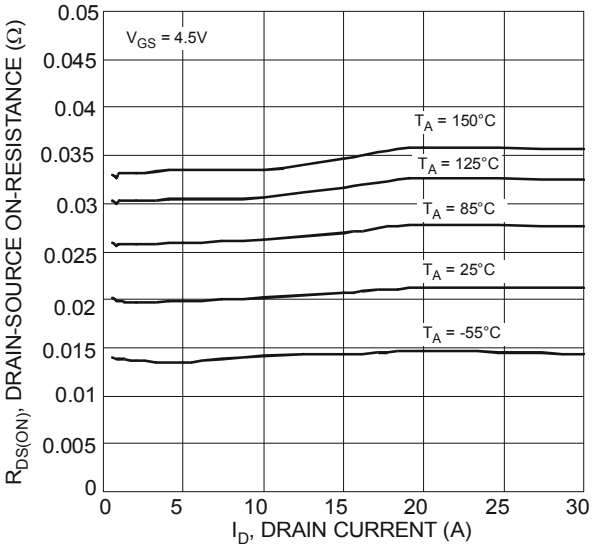


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

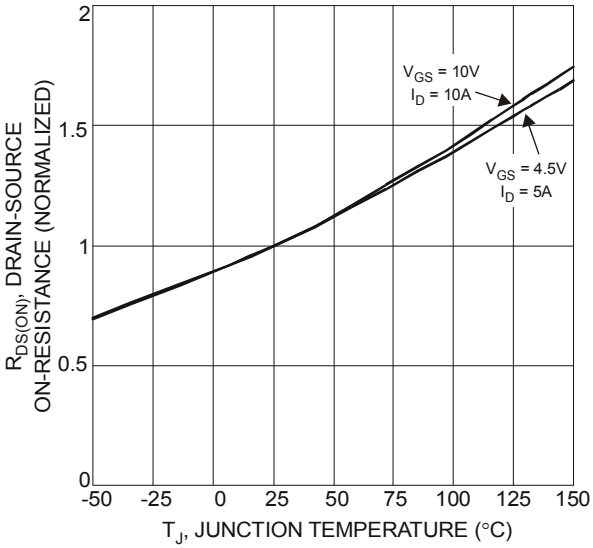


Figure 6 On-Resistance Variation with Temperature

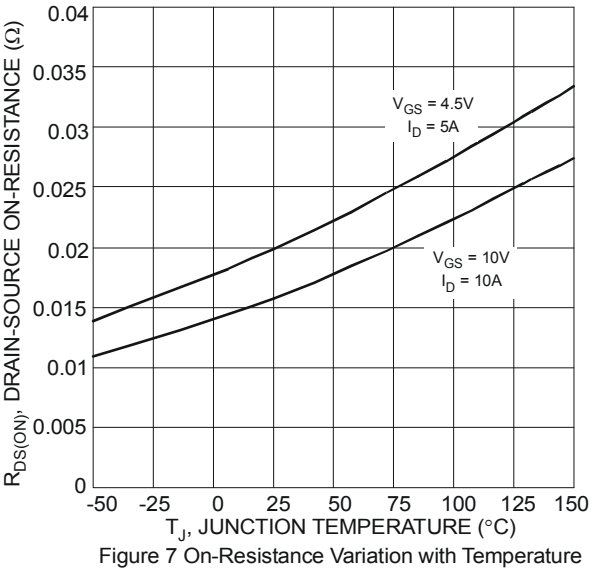


Figure 7 On-Resistance Variation with Temperature

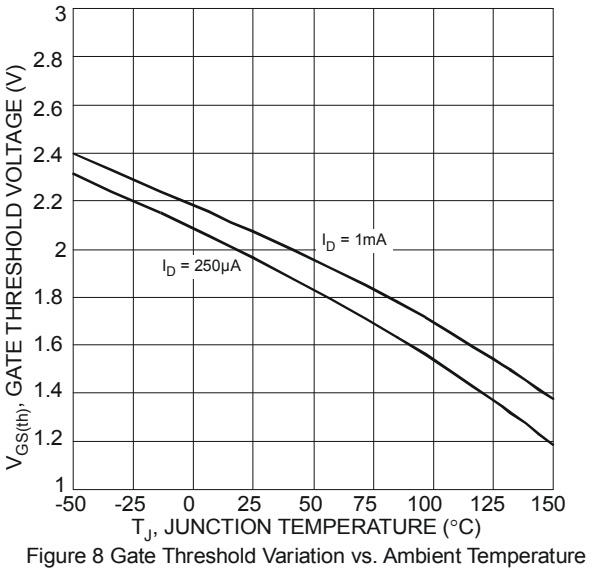


Figure 8 Gate Threshold Variation vs. Ambient Temperature

NEW PRODUCT

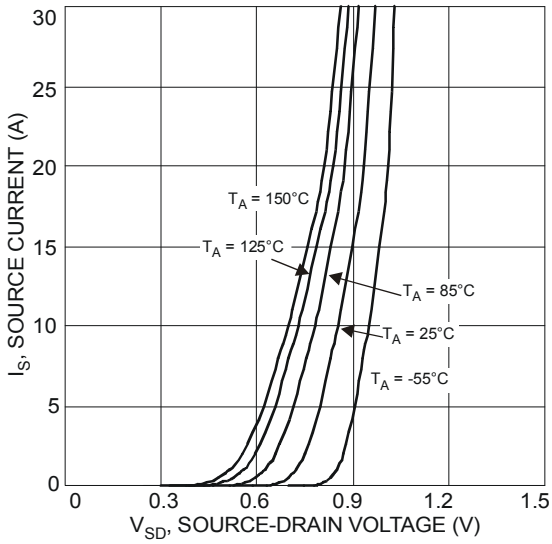


Figure 9 Diode Forward Voltage vs. Current

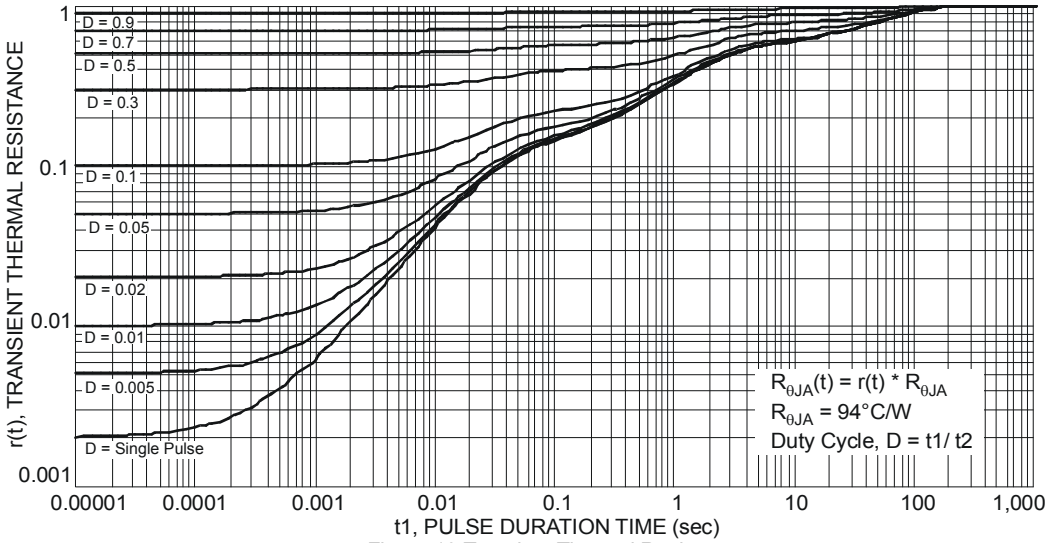


Figure 10 Transient Thermal Resistance

P-Channel Q1

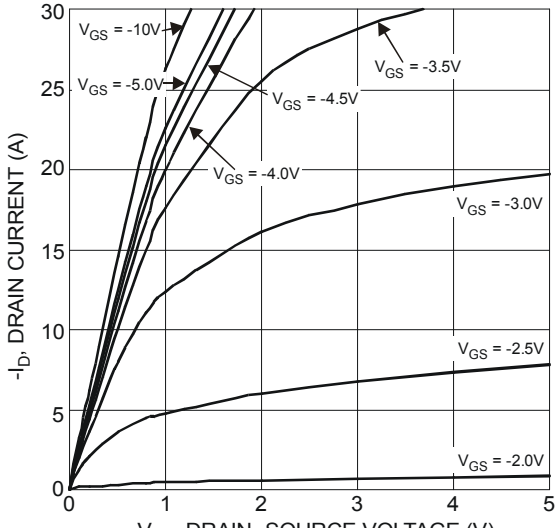


Figure 1 Typical Output Characteristics

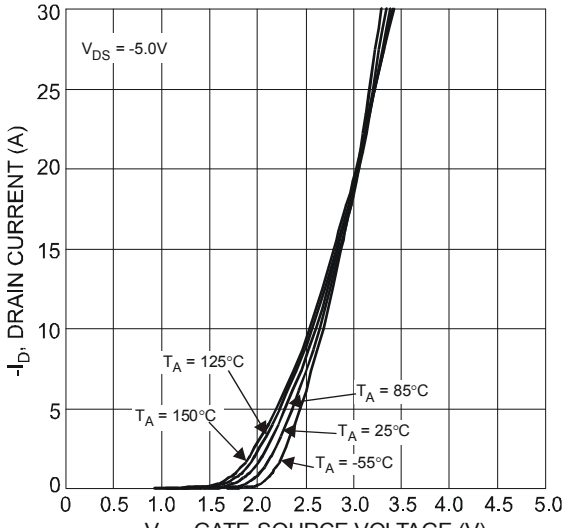


Figure 2 Typical Transfer Characteristics

NEW PRODUCT

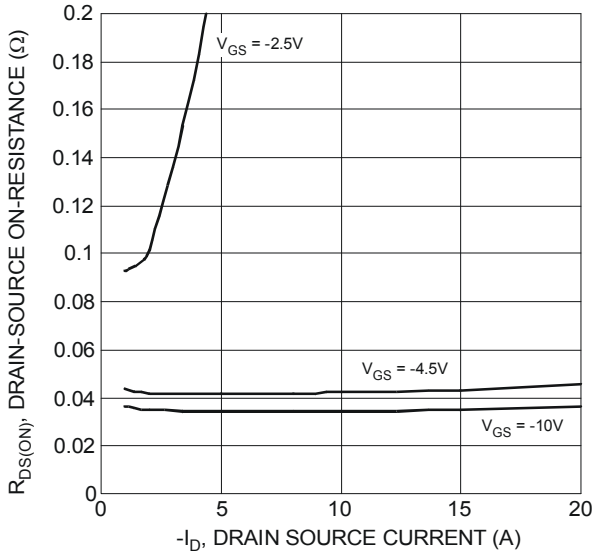


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

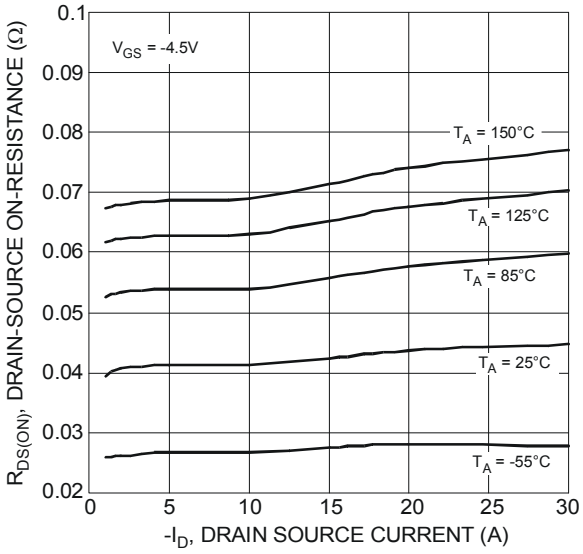


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

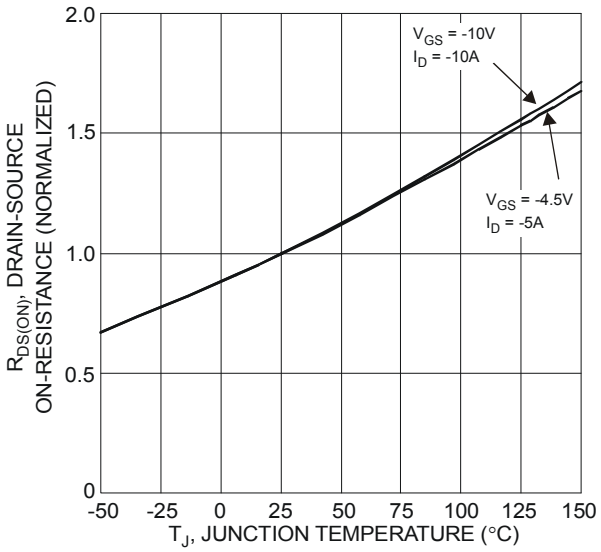


Figure 5 On-Resistance Variation with Temperature

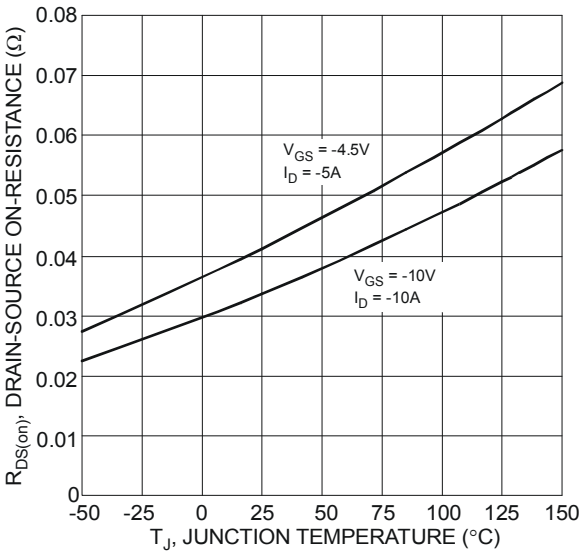


Figure 6 On-Resistance Variation with Temperature

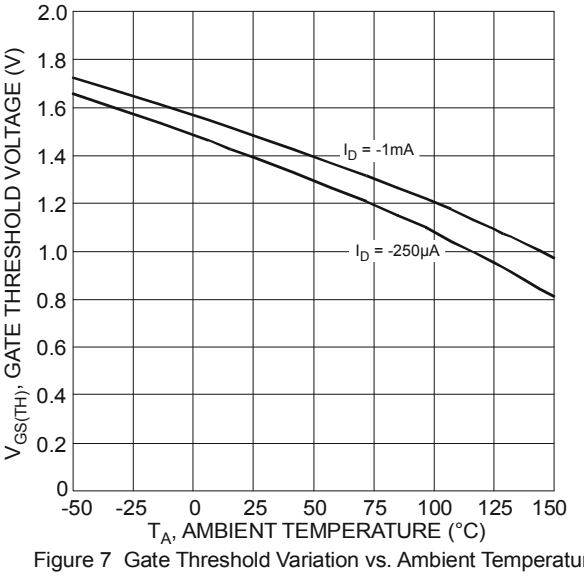


Figure 7 Gate Threshold Variation vs. Ambient Temperature

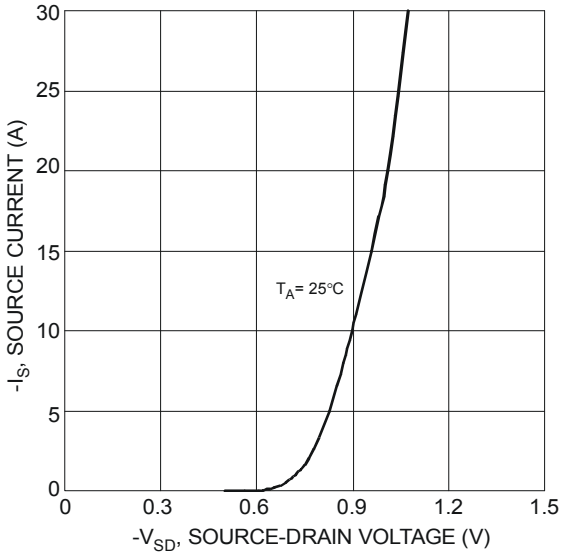


Figure 8 Diode Forward Voltage vs. Current

NEW PRODUCT

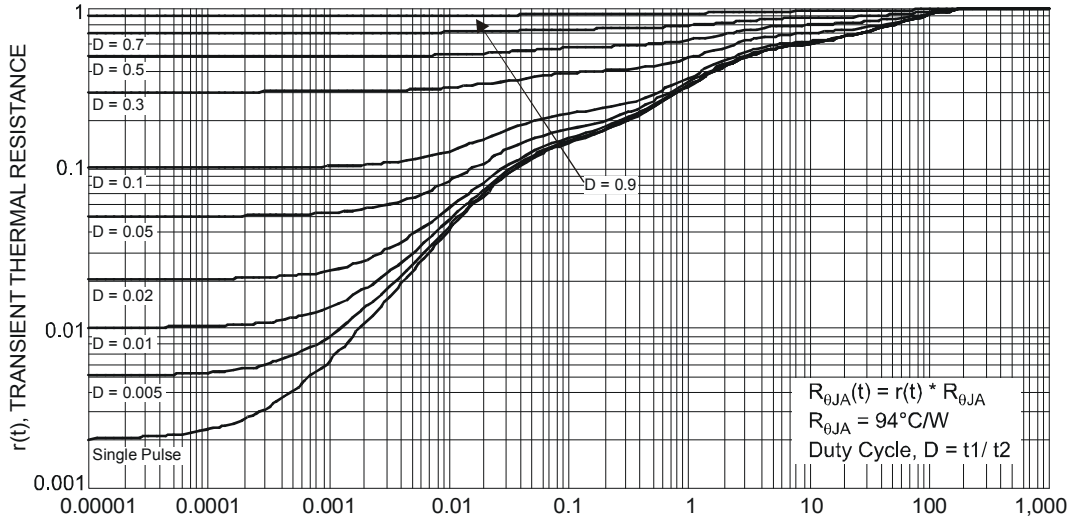
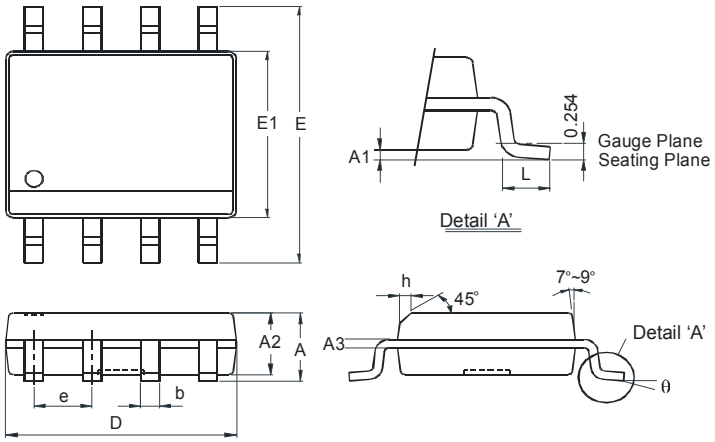


Figure 9 Transient Thermal Resistance

Package Outline Dimensions

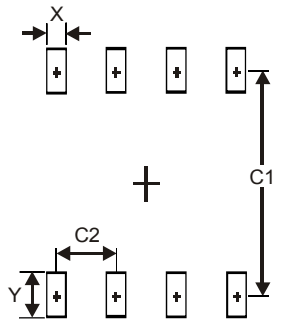
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8		
Dim	**Min**	**Max**
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

NEW PRODUCT

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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